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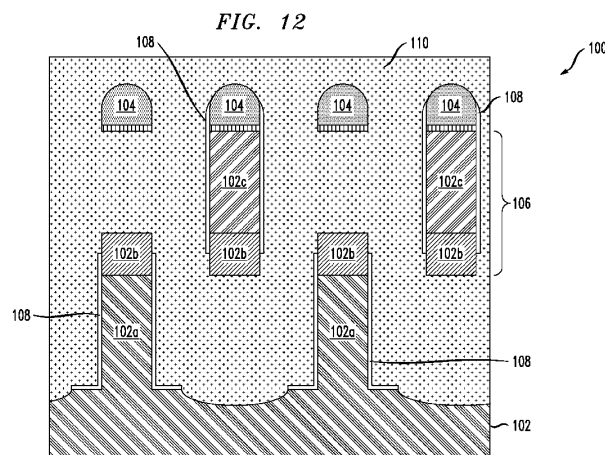
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(54) **Title:** STAGGERED STACKED VERTICAL CRYSTALLINE SEMICONDUCTING CHANNELS



(57) **Abstract:** A semiconductor structure (100) includes a first semiconductor channel having a plurality of vertical nanowires (106) and a second semiconductor channel having a plurality of vertical nanowires (106). The first semiconductor channel and the second semiconductor channel are configured to be in a stacked configuration. The plurality of vertical nanowires (106) of the first semiconductor channel are configured to be in alternating positions relative to the plurality of vertical nanowires (106) of the second semiconductor channel.

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